

General Descriptions

The WR1006 series are CMOS-based low-dropout, low-power linear regulators, offering 500mA/1A with low dropout voltage, high ripple rejection, high output accuracy and low supply current. The WR1006 series consist of an accurate voltagereference block, an error amplifier, a voltagesetting resistor net, a PMOSFET pass device, a thermal-shutdown circuit, and a current limit circuit with short protection.

The WR1006 series use a type of outstanding CMOS process to minimize the supply current. A low on-resistance PMOS pass device is equipped for lower dropout voltage. WR1006 also possess the CE function to save more energy and extend the battery life.

The WR1006 series can choose the output current between 500mA and 1A by setting the LCON pin to high or low.

The WR1006 series are available in the DFN1.2*1.6-8 package and.

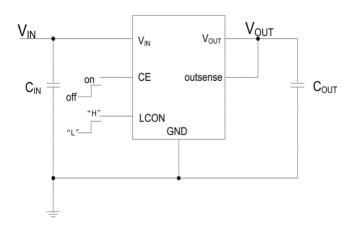
2. **Features**

- Wide Input Voltage Range: 2.5V to 5.5V
- Output Current: 500mA/1A optional
- Output Voltage Range: 1.0V to 3.3V
- Very Low I_Q: 130µA
- Excellent Load/Line Transient Response
- Line Regulation: 0.02% typical
- Built-in over current protection and thermal shutdown circuit
- Built-in Start from EN Current Suppression Circuit and Current Limit
- Reverse Current Protection
- Built-in Auto-discharging circuit (optional)

3. **Applications**

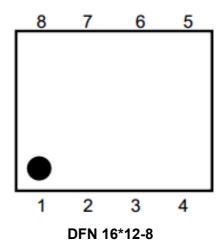
- MP3/MP4 Players
- Cellphones, radiophone, digital cameras
- Bluetooth, wireless handsets
- Others portable electronic device

4. **Typical Application**



5. Pin Configuration





6. Pin Description

PIN NAME		I/O	PIN FUNCTIONS
1	V _{OUT}	0	Regulated output voltage. A low equivalent series resistance (ESR) capacitor, typically 4.7µF, is required from OUT to
2	V _{OUT}	0	ground for stability. Place the output capacitor as close to the OUT and GND pins of the device as possible.
3	LCON	I	Output Current Limit Alternate ("H" =1A, "L" =500mA)
4	outsense	0	Feedback
5	GND	-	Common ground.
6	CE	I	Enable input. Active High.
7	V _{IN}	I	Input voltage supply. Bypass with a typical 4.7µF capacitor to
8	V_{IN}	I	GND. Place the input capacitor as close to the IN and GND pins of the device as possible.



Absolute Maximum Ratings[1] 7.

PARAMETER		RATING	UNIT
Input Volta	ge (V _{IN} Pin)	-0.3 to 6.0	V
Input Volta	ge (CE Pin)	-0.3 to 6.0	V
Input Voltage	e (LCON Pin)	-0.3 to 6.0	V
Output	Voltage	-0.3 to 6.0	V
Power Dissipation ^{[1][3]} , $P_D @T_A = 25^{\circ}C$ DFN-16*12-8		750	mW
Thermal Resistance ^{[1][2]} , DFN-16*12-8		165	°C/W
Junction Temperature		150	${\mathbb C}$
Lead Temperature Range		260	$^{\circ}$
Storage Temperature Range		-55 to 150	${\mathbb C}$
ESD Susceptibility HBM		±2000	V

NOTE1: Measured on 2cm x 2cm 2-layer FR4 PCB board, 1oz copper, no via holes on GND copper.

NOTE2: Measured according to JEDEC board specification. Detailed description of the board can be found in JESD51–7. **NOTE3:**Power dissipation is calculate by $P_{D(MAX)} = T_J - T_A / R_{\theta JA}$.

8. **Recommended Operating Conditions**

PARAMETER	RATING	UNIT
Input voltage range	2.5 to 5.5	V
EN Input voltage range	1.2 to 5.5	V
Nominal output voltage range	1.0 to 3.3	V
Output current	500mA/1A	mA
Input capacitor	4.7	μF
Output capacitor	4.7	μF
Operating temperature range	-40 to 85	${\mathbb C}$

ШАЧОN WR1006

Ultra low dropout, 500mA/1A, CMOS LDO

9. Electrical Characteristics (Full=-40 to 85 °C, VIN=VOUT+1.0V, IOUT=1mA, CIN=COUT=4.7µF, VLCON=VEN=VIN, unless otherwise noted.)

SYMBOL	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
V _{оит}	Output Voltage Range	V _{IN} =V _{OUT} +1.0V		0.98 V _{OUT}		1.02 V _{OUT}	V
V_{DO}	Dropout Voltage ¹	V _{OUT} =3.3V, I _{OUT} =500mA, Full V _{OUT} =3.3V, I _{OUT} =1A, Full V _{OUT} =3.0V, I _{OUT} =500mA, Full V _{OUT} =3.0V, I _{OUT} =1A, Full V _{OUT} =1.8V, I _{OUT} =500mA, Full V _{OUT} =1.8V, I _{OUT} =1A, Full			65 130 65 130 250 300		mV
I	Output Current Limit	V _{IN} =V _{OUT} +0.5V	LCON= "L"	500			mA
l _{out}	Output Current Limit	VIN-VOUT+U.5V	LCON= "H"	1000			mA
I _{SHORT}	Short Current Limit	V _{OUT} =0V	LCON="H"		160 80		mA
		V _{IN} =V _{OUT} +0.5V	LCON="H" 1mA≤I _{OUT} ≤1A		10		
LDR	Load Regulation ²	, , ,	LCON="L" 1mA≤I _{OUT} ≤0.5 A		5		mV
LNR	Line Regulation	V _{OUT} +1V≤V _{IN} ≤5.5V (V _{IN} ≥UVLO)			5	10	mV
ΙQ	Quiescent Current	V_{OUT} =3.3 V , I_{OUT} =0 mA , T_{A} =25 $^{\circ}$ C			160		μA
I _{SHDN}	Standby Current	V _{CE}	V _{CE} =0V		1	3	μΑ
I_{REV}	Reverse Current	V _{OUT} =V _{OSET} +1 V _{IN} =	V,V _{CE} =0V, =0V		4.5	10	μA
I _{RUSH}	Start from EN	CC mode	LCON="H"		500		mA
IKUSH	Current Limit		LCON="L"		300		ША
PSRR	Power Supply Ripple Rejection	f=1kHz, Ripple=0.2Vp-p, $V_{IN}=V_{SET}+1.0V$, $I_{OUT}=10mA$, $T_A=25$ °C			60		dB
e _{NO}	Output noise		z to 100KHz, nA,T _A =25 ° C		50		μV _{RMS}
	voltage (V _{OUT} =3V)	BW=10Hz to 100KHz, I _{OUT} =10mA,T _A =25 ° C			80		P ∧ KW2
$\frac{\Delta \ V_{OUT}}{\Delta \ T_A * V_{OUT}}$	Output Voltage Temperature Coefficient	-40 °C≤T _A ≤85 °C			90		ppm/º C
V_{ENH}	EN high voltage (enabled)	V _{IN} =5.5V, I _{OUT} =1mA, Full		1.2			V
V_{ENL}	EN low voltage (disabled)	V _{IN} =5.5V, I _{OUT} =1mA, Full				0.4	V

Electrical Characteristics (Full=-40 to 85 °C.Vin=Vout+1.0V. lout=1mA. Cin=Cout=4.7uF. Vlcon=Ven=Vin, unless otherwise noted.)

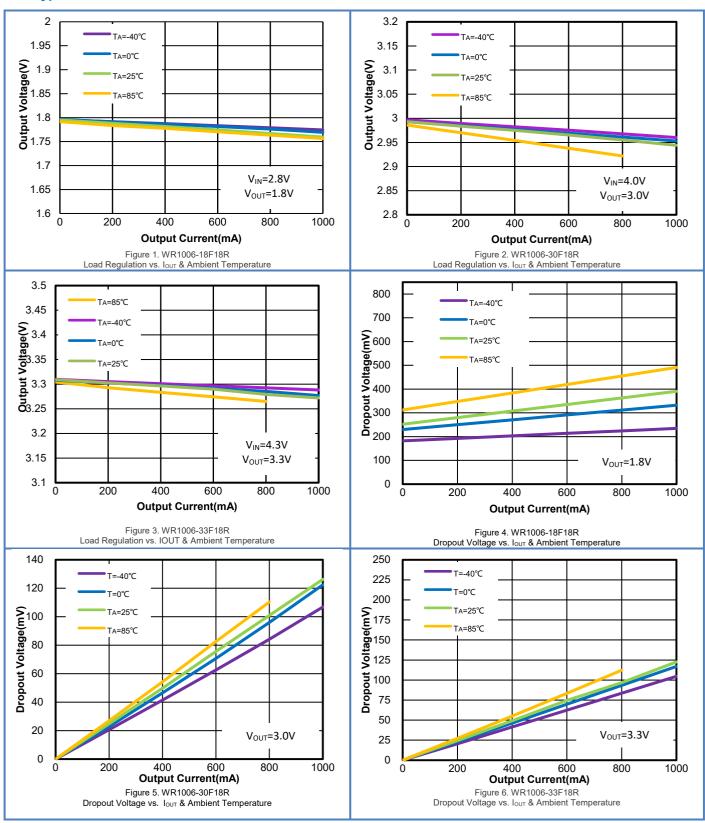
SYMBOL	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{LCON} LCON Pull-down Current				0.2	1	μΑ
V _{LCONH} LCON Input Voltage High			1.2			V
V_{LCONL}	LCON Input Voltage Low				0.4	V
T _{SD}	Thermal shutdown threshold			165		°C
ΔT_{SD}	Thermal shutdown hysteresis			30		°C
R _{DIS}	Output Discharge resistance	V_{IN} =4.0V, V_{CE} =0V, T_{A} =25°C		60		Ω

Note1: The dropout voltage is defined as $(V_{IN}-V_{OUT})$ when V_{OUT} is $V_{OUT(NOM)}^*98\%$.

Note2: The Load regulation is measured using pulse techniques with duty cycle < 5%.

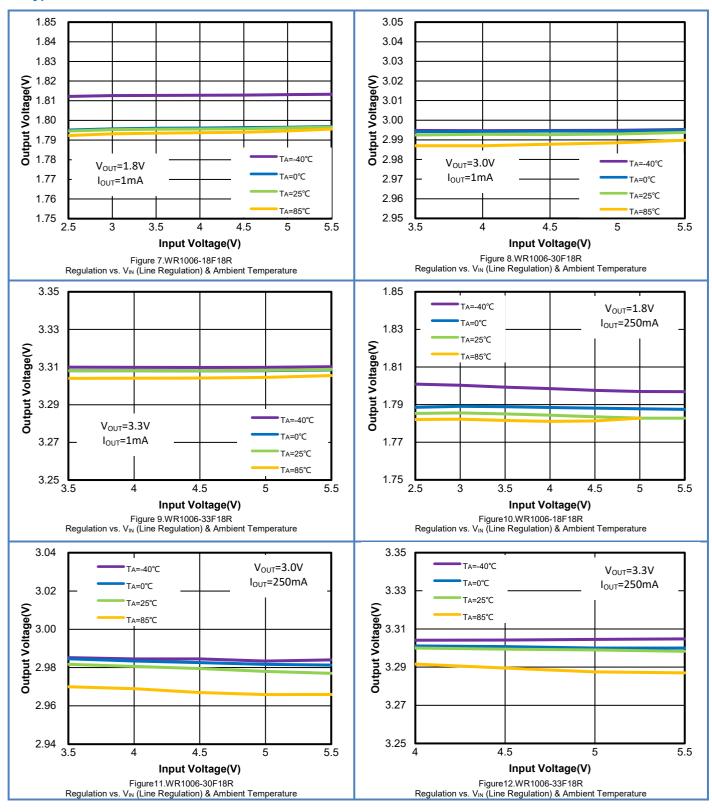
Ultra low dropout, 500mA/1A, CMOS LDO

10. Typical Performance Characteristics(Ta=-40 to 85 °C, Vin=Vout+1.0V, Cin=Cout=4.7 µF, VLCON=VEN=Vin, unless otherwise noted)



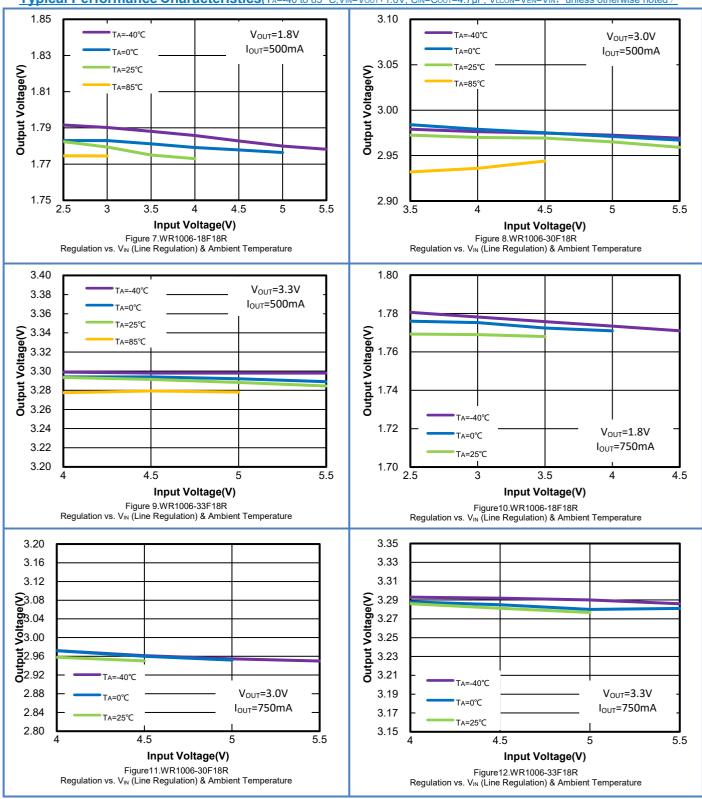
Ultra low dropout, 500mA/1A, CMOS LDO

Typical Performance Characteristics(T_A=-40 to 85 °C, V_{IN}=V_{OUT}+1.0V, C_{IN}=C_{OUT}=4.7µF, V_{LCON}=V_{EN}=V_{IN}, unless otherwise noted)



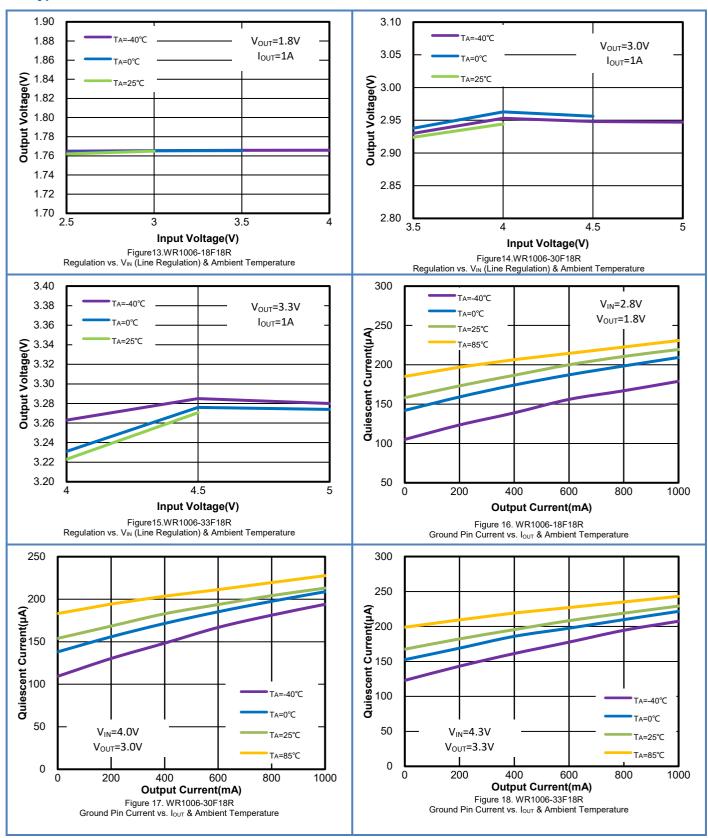
Ultra low dropout, 500mA/1A, CMOS LDO

Typical Performance Characteristics (Ta=-40 to 85 °C, Vin=Vout+1.0V, Cin=Cout=4.7 µF, Vlcon=Ven=Vin, unless otherwise noted)



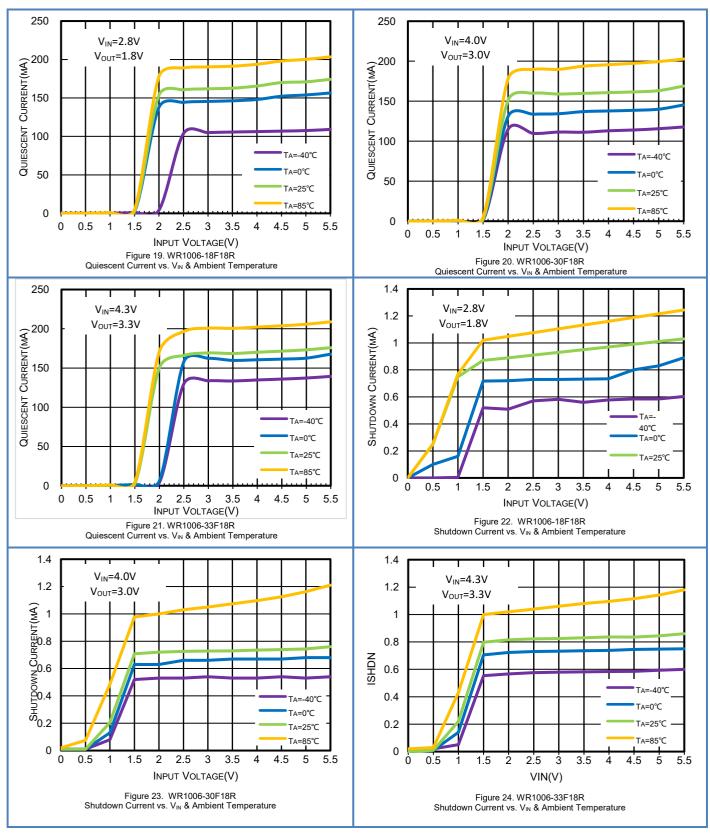
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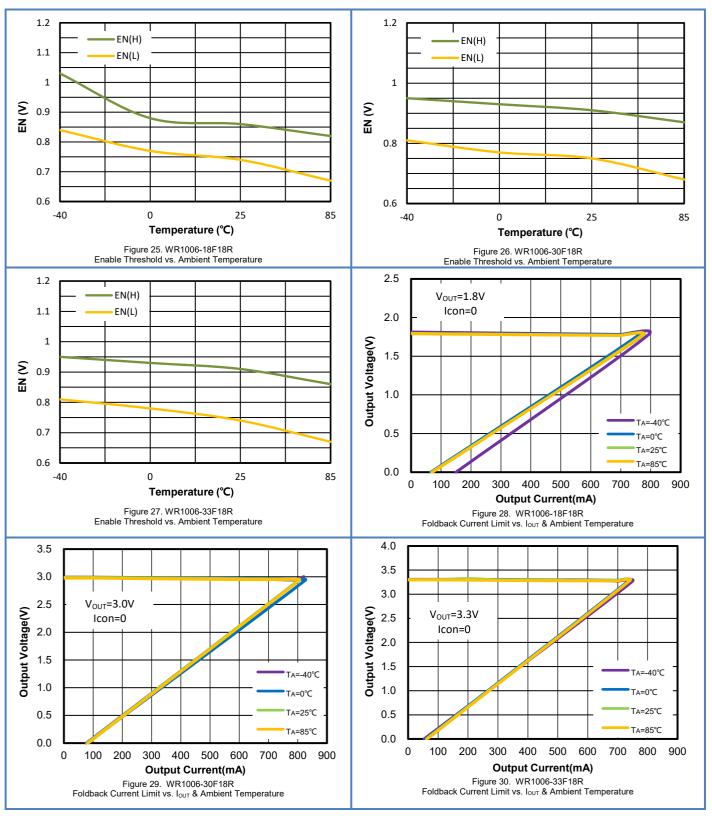
Ultra low dropout, 500mA/1A, CMOS LDO

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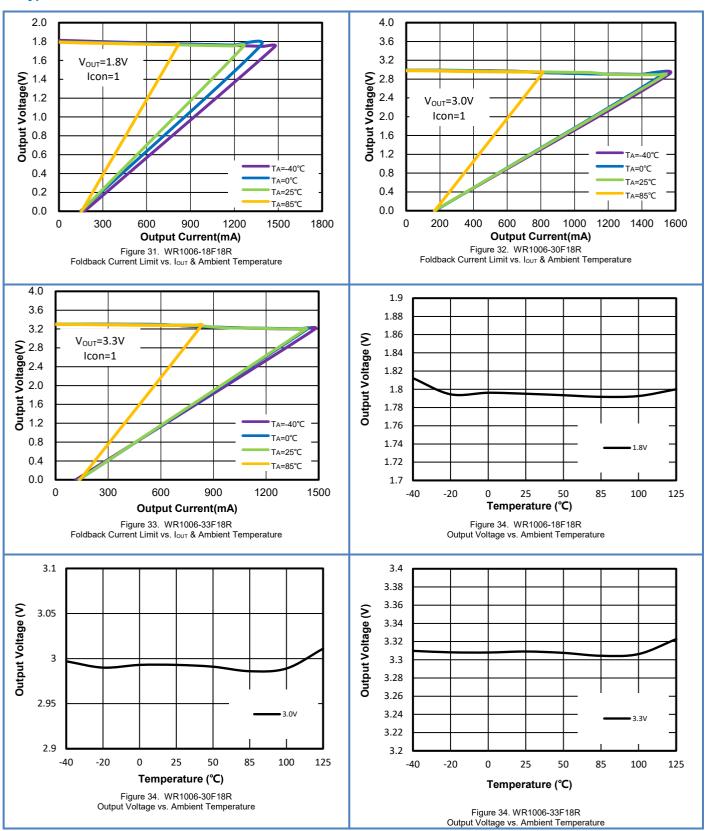
Ultra low dropout, 500mA/1A, CMOS LDO

Typical Performance Characteristics(T_A=-40 to 85 °C, V_{IN}=V_{OUT}+1.0V, C_{IN}=C_{OUT}=4.7µF, V_{LCON}=V_{EN}=V_{IN}, unless otherwise noted)



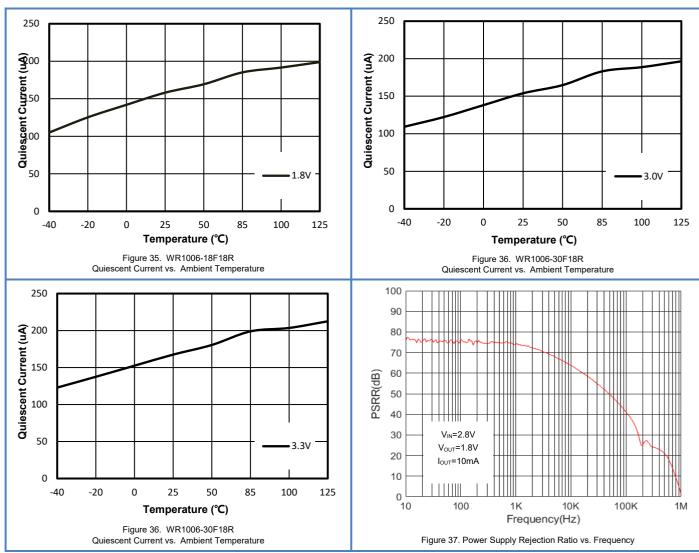
Ultra low dropout, 500mA/1A, CMOS LDO

Typical Performance Characteristics(Ta=-40 to 85 °C, Vin=Vout+1.0V, Cin=Cout=4.7 µF, VLCON=VEN=Vin, unless otherwise noted)



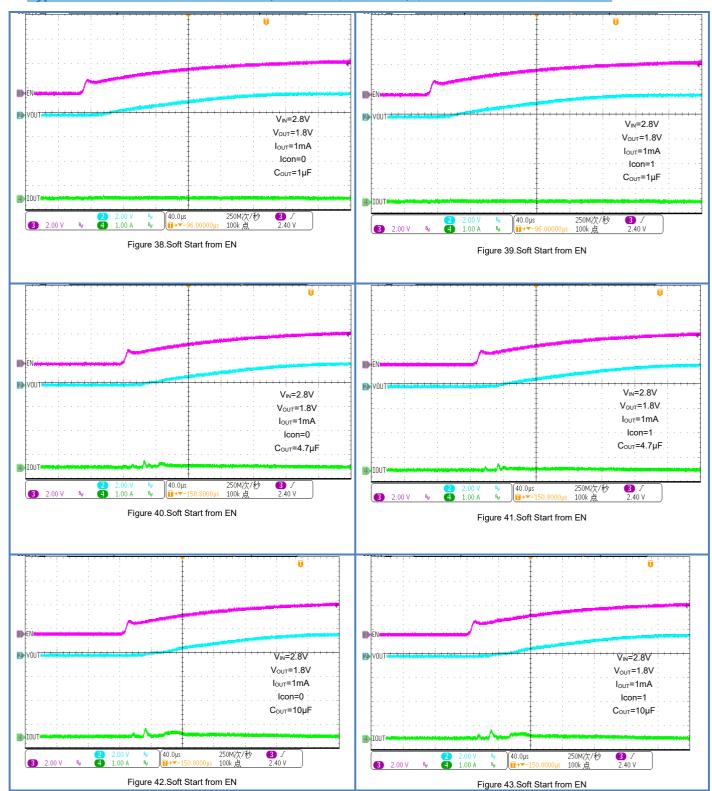
Ultra low dropout, 500mA/1A, CMOS LDO

Typical Performance Characteristics(T_A=-40 to 85 °C, V_{IN}=V_{OUT}+1.0V, C_{IN}=C_{OUT}=4.7µF, V_{LCON}=V_{EN}=V_{IN}, unless otherwise noted)



WR1006

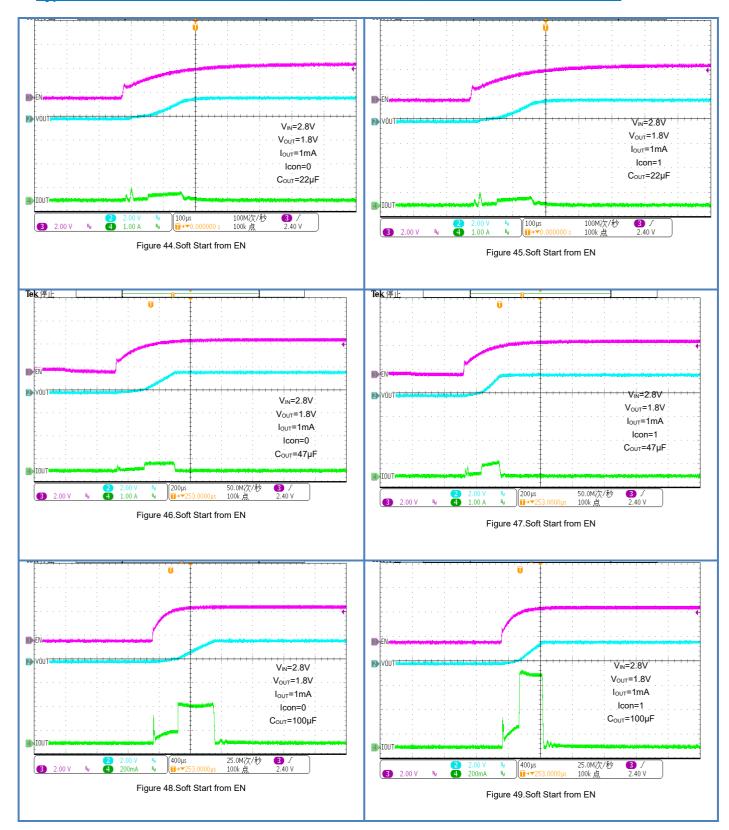
Ultra low dropout, 500mA/1A, CMOS LDO



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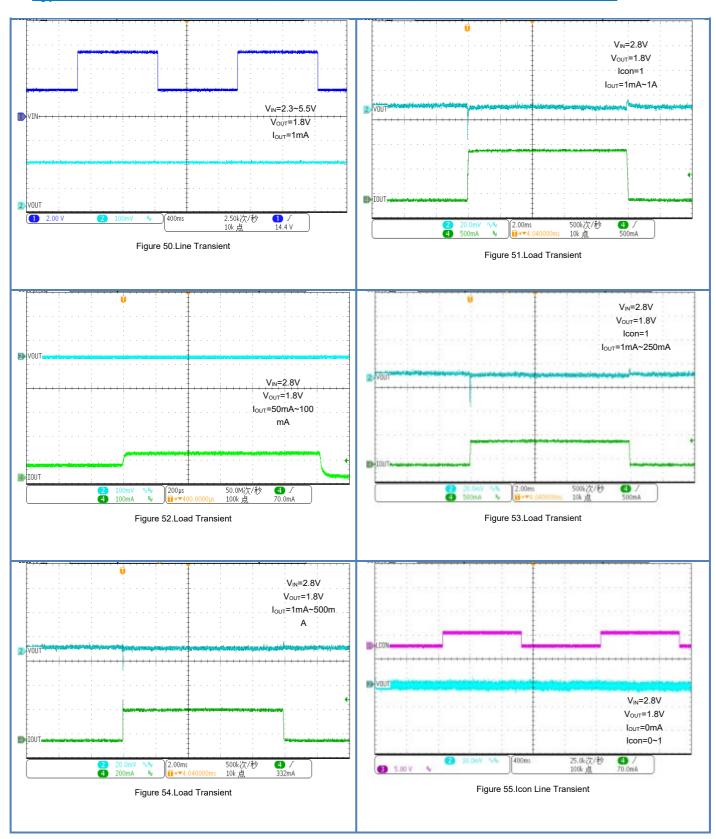
WR1006

Ultra low dropout, 500mA/1A, CMOS LDO



WR1006

Ultra low dropout, 500mA/1A, CMOS LDO



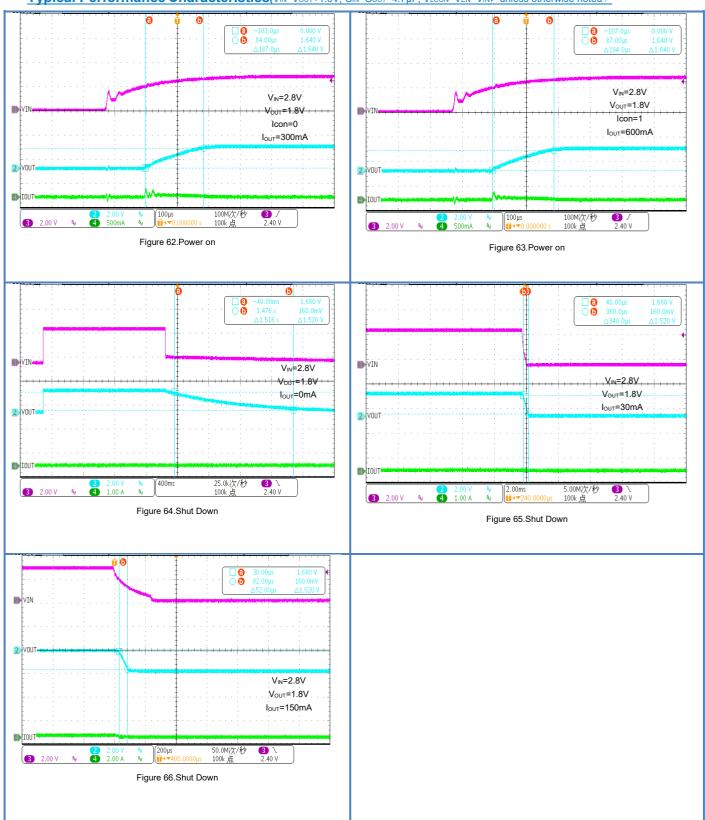


Typical Performance Characteristics(VIN=VOUT+1.0V, CIN=COUT=4.7µF, VLCON=VEN=VIN, unless otherwise noted) V_{IN}=2.8V V_{IN}=2.8V V_{OUT}=1.8V V_{OUT}=1.8V I_{OUT}=500mA I_{OUT}=150mA Icon=0~1 Icon=0~1 4 25.0k次/秒 100k 直 **a** / 3 5.00 V Figure 56.Icon Line Transient Figure 57.Icon Line Transient V_{IN}=2.8V V_{IN}=2.8V V_{OUT}=1.8V V_{out}=1.8V lcon=0 Icon=1 I_{OUT}=0mA I_{OUT}=0mA 2 VOUT 3 / 1.92 V 4 500mA Figure 58.Power on Figure 59.Power on V_{IN}=2.8V V_{IN}=2.8V V_{out}=1.8V V_{out}=1.8V Icon=1 Icon=0 I_{OUT}≑100mA I_{OUT}=100mA 3 2.00 V Figure 60.Power on Figure 61.Power on

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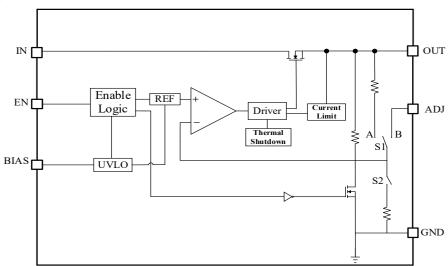


11. Function Description

11.1 Overview

The WR1006 series are CMOS-based low-dropout, low-power linear regulators, offering 500mA/1A with low dropout voltage, high ripple rejection, high output accuracy and low supply current. The WR1006 series consist of an accurate voltage-reference block, an error amplifier, a voltage-setting resistor net, a PMOSFET pass device, a thermal-shutdown circuit, and a current limit circuit with short protection.

11.2 Block Diagram



11.3 Feature Description

11.3.1 Output Voltage Accuracy

The WR1006 has an output voltage accuracy of 2%. Output voltage accuracy is defined as the maximum and minimum error in output voltage. This includes the errors introduced by internal reference, load regulation and line regulation differences over the full range of rated load and line operating conditions, taking into account differences between manufacturing lots.

11.3.2 Enable (EN)

When the input voltage of the enable pin is higher than the high enable voltage threshold, the device outputs normally. When the input voltage of the enable pin is lower than the low input voltage threshold of the EN pin, the device outputs shutdown. If you do not need to control the output voltage independently, connect the enable pin to the input of the device.

11.3.3 UVLO

When V_{IN} voltage is lower than UVLO, even when EN is high, the device will not start.

11.3.4 Dropout Voltage (VDO)

WR1006 has different Dropout voltages at high and low levels of Icon pins. Dropout voltage is defined as the V_{IN} - V_{OUT} at the rated maximum output current. When the input voltage is below the nominal output voltage, the output voltage varies with the input voltage. For CMOS regulators, the dropout voltage is determined by the $R_{\text{DS (ON)}}$ of the pass-FET.

The R_{DS} (ON) is calculated as follows:

RDS (ON)=VDO/IRATED



WR1006

11.3.5 Power Supply Rejection Ratio(PSRR)

PSRR, which stands for Power Supply Rejection Ratio, represents the ratio of the two voltage gains obtained when the input and output power supplies are considered as two independent sources.

The basic calculation formula is

PSRR = 20log(Ripple(in) / Ripple(out))

The units are in decibels (dB) and the logarithmic ratio is used.

The above equation shows that the output signal is influenced by the power supply in general, in addition to the circuit itself. PSRR is a quantity used to describe how the output signal is affected by the power supply; the larger the PSRR, the less the output signal is affected by the power supply.

As the level of integration continues to increase, the magnitude of supply current required is also increasing. End users want to extend battery life, i.e. they need very efficient DC/DC conversion processes, using more efficient switching regulators. However, switching regulators generate more—ripple in the power line than linear regulators.

The PSRR shows the ability of the LDO to suppress input voltage noise. For a clean, noise-free DC output voltage, use an LDO with a high PSRR.

Noise coupling from the input voltage to the internal reference voltage is the main cause of PSRR performance degradation. Using noise reduction capacitors at the input can effectively filter out noise and improve PSRR performance at low frequencies. The LDO can be used not only to regulate the voltage but also to provide an exceptionally clean DC supply for noise sensitive components.

The WR1006 is a high PSRR LDO that can be used not only for voltage regulation but also for noise cancellation in the power supply.

11.3.6 Noise

LDO noise can be divided into two main categories: internal noise and external noise. Internal noise is the noise generated inside the electronics; external noise is the noise transmitted from outside the circuit to the circuit. The error amplifier determines the PSRR of the LDO and therefore its ability to suppress external noise at the input; internal noise is always present at the output of the LDO.

In practice, minimising noise from the power supply is critical to system performance. In test and measurement systems, small fluctuations in power supply noise can alter the instantaneous measurement accuracy.

The WR1006 has a low noise reference, high PSRR to ensure that output noise is reduced during normal operation.

11.3.7 Foldback Current Limit (I_{CL})

In LDO circuits, if an output short circuit or excessive load current occurs, the device may be burned out. Especially in the case of a short circuit, not only is there too much current flowing through the regulator, but the voltage across the source drain of the regulator is also at its maximum, which is likely to burn out the regulator and make the device inoperable. The current limiting circuit used in LDO is a constant current limiting circuit, where the maximum load current that the LDO can supply is limited to a set constant I_{MAX} ,



and when an overload or short circuit occurs, the output current will be praintsined at Amexicaed the output voltage will be reduced to IMAXRLOAD.

However, if the external overload or short circuit condition lasts for a long time, the continuous high current will increase the device temperature and increase the power consumption of the whole system. To improve this situation, a foldback current limiting circuit can be used. In a foldback current limiting circuit, both the output current and the output voltage are gradually reduced when the output current reaches the set maximum current I_{MAX} . The output current is reduced to the set current threshold IFB and the output voltage is reduced to $I_{FBRLOAD}$. The output current is clamped to a smaller value in the event of an overload or short circuit and the system power consumption is reduced and the device temperature does not rise significantly.

The foldback current limiting circuit is essentially a constant current limiting circuit with an output voltage feedback loop, so that in the event of an overload or short circuit, the output current is gradually reduced due to the reduction in output voltage and eventually clamped at a smaller value.

WR1006 has different current limit values at high and low levels of Icon pins. More information on current limiting can be found in Electrical Characteristics Figure 28 to Figure 33.

11.3.8 Thermal Protection

The WR1006 contains a thermal shutdown protection circuit that implements the required switching gate circuit function through a thermal switch integrated inside the chip. The output current is turned off when the heat in the LDO is too high. Thermal shutdown occurs when the thermal junction temperature (TJ) of the energized crystal exceeds 165°C (typical). The thermal shutdown hysteresis ensures that the LDO resets (turns on) again when the temperature drops to 135°C (typical). The thermal time constant of the semiconductor chip is quite short, so when thermal shutdown is reached, the output turns on and off at a higher rate until the power dissipation is reduced.

The WR1006's internal protection circuitry is designed to prevent thermal overload conditions. This circuitry is not a substitute for a proper heat sink. Continuously putting the WR1006 into a thermal shutdown state will reduce the reliability of the device.

For reliable operation, limit the junction temperature to a maximum of 125°C. The thermal margin in a given layout is to be estimated. For good reliability, thermal shutdown must occur at least 35°C above the maximum expected ambient temperature condition of the application.

11.3.9 Reverse Current Protection Circuit

The WR1006 include a Reverse Current Protection Circuit, which stop the reverse current from V_{OUT} pin to V_{IN} pin or GND pin when V_{OUT} becomes higher than V_{IN} .

Following figure shows the load characteristics of each mode. When giving the V_{OUT} pin a constant voltage and decreasing the V_{IN} voltage,the V_{IN} voltage will become lower than V_{OUT} - V_{rev} _det, the reverse current protection starts to function to stop the load current. By increasing the V_{IN} voltage higher than V_{OUT} - V_{rev} _rel, the protection mode will be released to let the load current to flow. When V_{IN} voltage is between V_{OUT} and V_{rev} _det, the parasitic diode between V_{IN} pin and V_{OUT} pin becomes forward direction. As a result, the current flows from V_{OUT} pin to V_{IN} pin, and the maximum of the current.

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WR1006

Ultra low dropout, 500mA/1A, CMOS LDO

11.4 Functional Mode Of The Device

The device has three modes: normal, dropout, and disabled modes of operation.

The operating conditions of each mode are listed in the table below.

Operating conditions of each mode

FUNCTIONAL MODE	CONDITIONS					
FONCTIONAL MODE	V _{IN}	V _{EN}	I _{OUT}	TJ		
Normal	$5.5V > V_{IN} > V_{OUT(nom)} + V_{DO}$	$V_{EN} > V_{IH(EN)}$	I _{OUT} < I _{CL}	$T_J < T_{sd}$		
Dropout	$V_{IN} < V_{OUT(nom)} + V_{DO}$	$V_{EN} > V_{IH(EN)}$	I _{OUT} < I _{CL}	$T_J < T_{sd}$		
Disabled	V _{IN} < V _{UVLO}	V _{EN} < V _{IL(EN)}	_	$T_J > T_{sd}$		

11.4.1 Normal Mode

Normal operating mode requires that both of the following conditions are met.

- 1. The input voltage is greater than the rated output voltage plus the differential voltage ($V_{OUT}(nom) + VDO$) and is less than 5.5V.
- 2. The enable voltage has previously exceeded the enable rise threshold voltage and has not fallen below the enable fall threshold.
 - 3. The output current is less than the current limit ($I_{OUT} < I_{CL}$).
 - 4. The device junction temperature is less than the thermal shutdown temperature ($T_J < T_{sd}$).

11.4.2 Dropout Mode

If the input voltage is below the rated output voltage plus a specified dropout voltage, but all other conditions are met for normal operation, the device operates in the dropout state and the output voltage tracks the input voltage. Because the transient performance of the device is significantly reduced through the device being in the triode state, the output current is no longer controlled. Line or load transients during power down can result in large output voltage deviations.

11.4.3 Disabled

The WR1006 can be turned off by forcing the enable pin low, typically with an enable voltage below 0.4V, at which point the pass device is turned off, internal circuits are shutdown, and the output voltage is actively discharged to ground through an internal resistor from output to ground.

12. Application

Note: The information in the Applications section below is not part of WAY-ON's product specifications and WAY-ON does not guarantee its accuracy or completeness. The customer is responsible for determining the suitability of the component for its intended use and should verify and test its design implementation to confirm system functionality.

12.1 Application Information

The WR1006 is a linear voltage regulator with an input voltage of 2.0 V to 5.5 V and an output voltage of 1.8 V to 3.3 V. The accuracy is 2% for output voltages . The maximum output current is 500 mA at Icon is low and 1A at Icon is high. The efficiency of a linear voltage regulator is determined by the ratio of the output voltage to the input voltage, so in order to achieve high efficiency, the differential voltage ($V_{IN}-V_{OUT}$) must be as small as possible. This section discusses how best to use this device in practical applications.



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Ultra low dropout, 500mA/1A, CMOS LDO

12.1.1 Start-Up

12.1.1.1 Inrush Current Limit

Constant slope circuit is included in the WR1006 to prevent the overshoot of the output voltage. If inrush current increases due to the large capacitance of _{COUT}, the operation mode will be shift from Constant Slope (CS) mode to Constant Current (CC) mode. The CC mode maintains a constant inrush current. In the CC mode, ton varies with the size of COUT and the load current.

12.1.1.2 Automatic Discharge

The WR1006 has an internal pull-down MOSFET that connects a discharge resistor from V_{OUT} to ground to actively release the output voltage when the device is disabled.

12.1.2 Capacitor Recommendation

The WR1006 uses ceramic capacitors with low equivalent series resistance (ESR) at the $V_{\rm IN}$ and $V_{\rm OUT}$ pins to increase its stability. Multilayer ceramic capacitors are recommended. These capacitors also have limitations, and ceramic capacitors with X7R-, X5R-, and COG-rated dielectric materials have

relatively good capacitance stability at different temperatures. WR1006 is designed to use ceramic capacitors of 1 μ F or larger at the input and output. Place C_{IN} and C_{OUT} as close to the IN and OUT pins as possible to minimize trace inductance from the capacitor to the device.

Increasing the input capacitance can reduce the transient input drop during start-up and load current. If the C_{OUT} produces high Q peak effects during transients, using only very large ceramic input capacitors can cause unwanted ringing at the OUT side, which requires well-designed short interconnects to the upstream supply to reduce ringing. Using a tantalum capacitor with an ESR of several hundred milliohms in parallel with the ceramic input capacitor can avoid unwanted ringing. The load step transient response is the output voltage response of the LDO to a step change in load current. A larger output capacitor reduces any voltage dips or spikes that occur during the load step, but at the same time the control loop bandwidth is reduced, which slows the response time.

Because, the LDO cannot consume charge, the control loop must close through the FET when the output load is removed or greatly reduced and wait for any excess charge to be depleted.

12.1.3 Power Dissipation(PD)

The reliability of the circuit requires reasonable consideration of the power dissipation of the device, the location of the circuit on the PCB, and the proper sizing of the thermal plane. The regulator should be surrounded by no other heat generating devices as much as possible. The power dissipation of the regulator depends on the input and output voltage difference and the load conditions.

PD can be calculated using the following equation:

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT}$$

Using the proper input voltage minimizes the power dissipation, resulting in greater efficiency. To obtain the lowest power dissipation, use the minimum input voltage required for normal output voltage.

The maximum power dissipation determines the maximum allowable ambient temperature (T_A) of the device. Power dissipation and junction temperature are typically related to the junction-ambient thermal resistance (θ_{JA}) and ambient air temperature (T_A) of the PCB and package and are calculated as follows

$$T_J = T_A + (\theta_{JA} \times P_D)$$

The thermal resistance (θ_{JA}) depends primarily on the thermal dispersion capability of the PCB design. The total copper area, copper weight, and the location of the plane all affect the thermal dispersion capability, and the PCB and copper laydown area can only be used as a relative measure of the package's thermal performance.

12.1.4 Estimate the temperature of the junction

As recommended by JEDEC, the psi (Ψ) thermal metrics are used to estimate the junction temperature of the LDO in PCB board applications. These metrics are relative estimates of the junction temperature in actual applications. The thermal indicators Ψ_{JT} or Ψ_{JB} are given in the thermal information table and can be used according to the following equation.

$$\Psi_{JT}: T_J = T_T + \Psi_{JT} \times P_D$$

$$\Psi_{JB}: T_J = T_B + \Psi_{JB} \times P_D$$

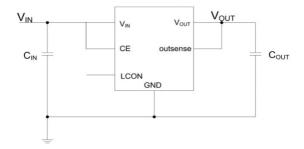
Notes.

- P_D is the power dissipated.
- T_T is the temperature at the top center of the device package.
- T_B is the PCB surface temperature measured 1 mm from the device package and centered on the package.

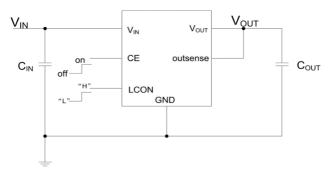
12.2 Typical Application

This section discusses the application of the WR1006 in the circuit. The following figure shows the schematic of the application circuit.

Circuit schematic 1: V_{OUT} normally open, no control.



Circuit schematic 2: V_{OUT} control by external voltage to EN.



 C_{IN} and C_{OUT} are to be selected with the recommended appropriate capacitance. $1\mu F$ ceramic capacitors are selected for both C_{IN} and C_{OUT} to help balance the charge needed to charge the output capacitor during startup, thus reducing the input voltage drop.

Ultra low dropout, 500mA/1A, CMOS LDO

13. Power supply recommendation

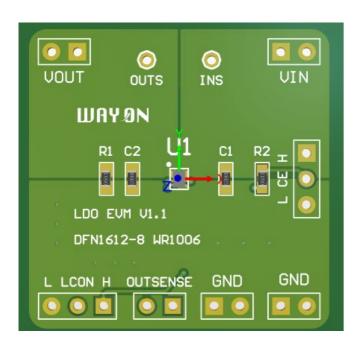
The WR1006 has a V_{IN} range of between 2.0 V and 5.5 V and an input capacitance of $1\mu F$. The input voltage should have some redundancy to ensure a stable output voltage when the load fluctuates. If the input supply is noisy, additional input capacitors can be used to improve the noise performance of the output.

14. Layout Guidelines

The principle of LDO design is to place all components on the same side of the board and connect them as close as possible to their respective LDO pins. Connect the C_{IN} and C_{OUT} grounds, with all LDO ground pins as close together as possible, through a wide copper surface. Using through-holes and long wires for connections is strongly discouraged and can seriously affect system performance.

To improve thermal performance, an array of thermal vias is used to connect the thermal pad to the ground plane. A larger ground plane improves the thermal performance of the device and reduces the operating temperature of the device.

Layout Example:



15. Evaluation Modules

Evaluation Modules (EVMs) are available to help evaluate initial circuit performance. We have evaluation modules for different packages, you can contact us by phone or address at the end to get the evaluation module or schematic.

The module names are listed in the table below.

Name Package		Evaluation Module		
WR1006	DFN16*12-8	WAYON LDO EVM V1.1 -DFN16*12-8		



WR1006

Ultra low dropout, 500mA/1A, CMOS LDO

16. Naming conventions

WR AA BB-CC DDD E

WR: WAYON Regulator **AA:** 10 - Output Current, 1A

BB: Serial number

CC: Output Voltage/AD-Output Voltage, Adjustable Voltage

DDD: F18- Package, DFN1612-8L

E: R-Reel & T-tube

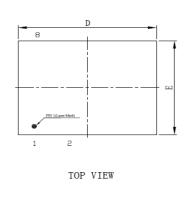
17. Electrostatic discharge warning

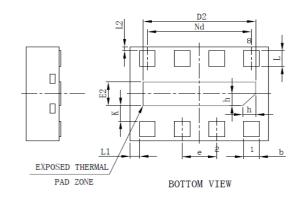
ESD can cause irreversible damage to integrated circuits, ranging from minor performance degradation to device failure. Precision ICs are more susceptible to damage because very minor parameter changes can cause the device to be out of compliance with its published specifications. WAY-ON recommends that all ICs be handled with proper precautions. Failure to follow proper handling practices and installation procedures may damage the IC.

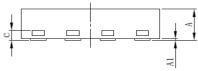


18. Package Information

DFN16*12-8







OVMDOL	DIMENSIONS IN MILLIMETERS				
SYMBOL	MIN	NOM	MAX		
Α	0.35	-	0.40		
A 1	0	0.02	0.05		
b	0.13	0.18	0.23		
С		0.127REF			
D	1.55				
D2	1.25	1.35			
е	0.40BSC				
Nd	1.20BSC				
E	1.15 1.20 1		1.25		
E2	0.25	0.25 0.30 0.15 0.20			
L	0.15				
L1	0.06 0.11		0.16		
L2	0.05REF				
h	0.10 0.15 0.2		0.20		
k	0.15				



19. Ordering Information

Part Number	Output Voltage	Package	Packing Quantity	Marking
WR1006-18F18R	1.8V	DFN-8	3k/Reel	006 18
WR1006-28F18R	2.8V	DFN-8	3k/Reel	006 28
WR1006-30F18R	3.0V	DFN-8	3k/Reel	006 30
WR1006-33F18R	3.3V	DFN-8	3k/Reel	006 33

^{*} XXXX is variable.



STATEMENTS

WAY-ON provides data sheets based on the actual performance of the device, and users should verify actual device performance in their specific applications. The device characteristics and parameters in this data sheet can and do vary from application to application, and actual device performance may change over time. This information is intended for developers designing with WAY-ON products. Users are responsible for selecting the appropriate WAY-ON product for their application and for designing and verifying the application to ensure that your application meets the appropriate standards or other requirements, and users are responsible for all consequences. Specifications are subject to change without notice.

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For additional information, please contact your local Sales Representative.

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